Vincotech

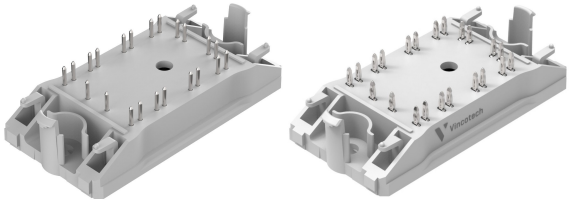
V23990-P629-L57-PM
V23990-P629-L57Y-PM
datasheet

***flow*BOOST 0** **1200 V / 50 A**

Features

- High efficiency dual boost
- Ultra fast switching frequency
- Low Inductance Layout
- 1200V IGBT and 1200V SiC diode
- Antiparallel IGBT protection diode with high current

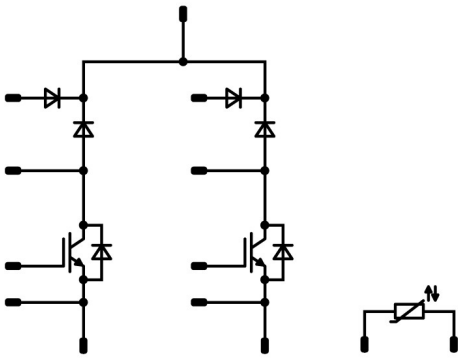
flow 0 12mm housing



Target applications

- Solar Inverters

Schematic



Types

- V23990-P629-L57-PM
- V23990-P629-L57Y-PM

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Boost Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C	$T_j = T_{jmax}$ T_s = 80 °C	52	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	135	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V V_{CC} = 800 V T_j = 150 °C	10	µs
Maximum junction temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Boost Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ T_s = 80 °C	28	A
Repetitive peak forward current	I_{FRM}		104	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave t_p = 10 ms T_j = 25 °C	184	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	103	W
Maximum junction temperature	T_{jmax}		175	°C
Boost Sw. Protection Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ T_s = 80 °C	33	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave t_p = 10 ms T_j = 150 °C	200	A
Surge current capability	I^2t		200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	44	W
Maximum junction temperature	T_{jmax}		150	°C
ByPass Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$ T_s = 80 °C	33	A
Surge (non-repetitive) forward current	I_{FSM}	50 Hz Single Half Sine Wave t_p = 10 ms T_j = 150 °C	200	A
Surge current capability	I^2t		200	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	44	W
Maximum junction temperature	T_{jmax}		150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
		AC Voltage t_p = 1 min	2500	V
Creepage distance			min. 12,7	mm
Clearance		Solder pin / Press-fit pin	9,55 / 9,15	mm
Comparative Tracking Index	CTI		> 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}$			0,0017	25	5,3	5,8	6,3	V
Collector-emitter saturation voltage	V_{CEsat}		15		50	25 125 150	1,78	2,04 2,38 2,46	2,42	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			1	µA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							4		Ω
Input capacitance	C_{ies}	f= 1 Mhz	0	25		25		2770		pF
Reverse transfer capacitance	C_{res}							160		
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,70		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 8 Ω R_{goff} = 8 Ω	0 / 15	700	50	25 125 150		30 30 30		ns
Rise time	t_r					25 125 150		20 21 22		
Turn-off delay time	$t_{d(off)}$					25 125 150		335 388 408		
Fall time	t_f					25 125 150		20 56 67		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 0,3 µC Q_{rFWD} = 0,5 µC Q_{rFWD} = 0,5 µC				25 125 150		2,268 2,528 2,569		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,970 3,327 3,752		

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Diode										
Static										
Forward voltage	V_F				20	25 125		1,46 1,80	1,8	V
Reverse leakage current	I_R			1200		25			600	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,92		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 2745 A/µs di/dt = 2604 A/µs di/dt = 2496 A/µs	0 / 15	700	50	25 125 150		11 12 12		A
Reverse recovery time	t_{rr}					25 125 150		10 12 13		ns
Recovered charge	Q_r					25 125 150		0,315 0,478 0,517		µC
Reverse recovered energy	E_{rec}					25 125 150		0,105 0,210 0,230		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		3203 2883 2460		A/µs
Boost Sw. Protection Diode										
Static										
Forward voltage	V_F				25	25 125		1,22 1,21		V
Reverse leakage current	I_R			1600		25			50	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,59		K/W
ByPass Diode										
Static										
Forward voltage	V_F				25	25 125		1,22 1,21		V
Reverse leakage current	I_R			1600		25			50	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,59		K/W

Characteristic Values

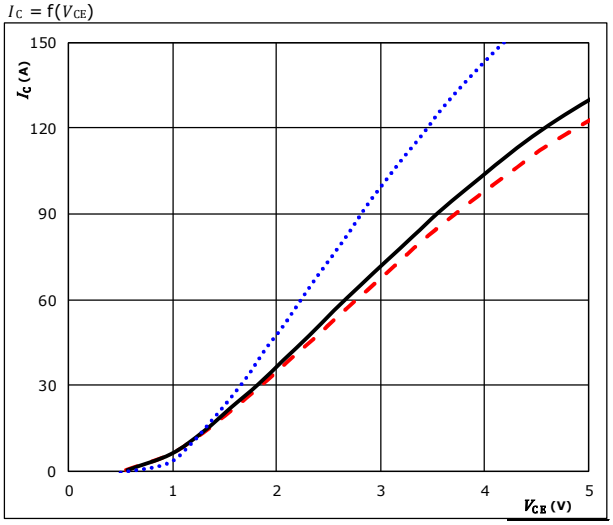
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1486 Ω				100	-12		+14	%
Power dissipation	P					25		200		mW
Power dissipation constant						25		2		mW/K
B-value	$B_{(25/50)}$	Tol. ±3%				25		3950		K
B-value	$B_{(25/100)}$	Tol. ±3%				25		3998		K
Vincotech NTC Reference									B	

Boost Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

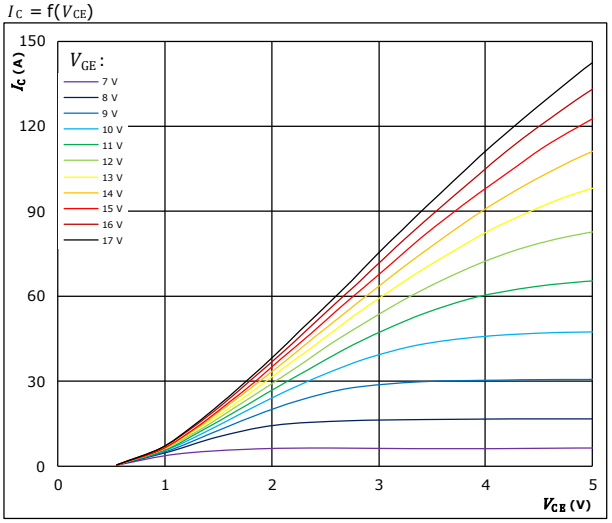


t_p =	250	µs		25 °C	
V_{GE} =	15	V	T_j:	125 °C	
				150 °C	

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

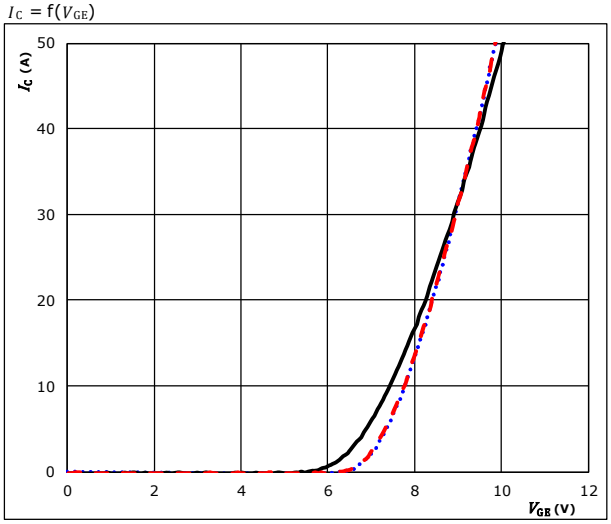


t_p =	250	µs
T_j =	150	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

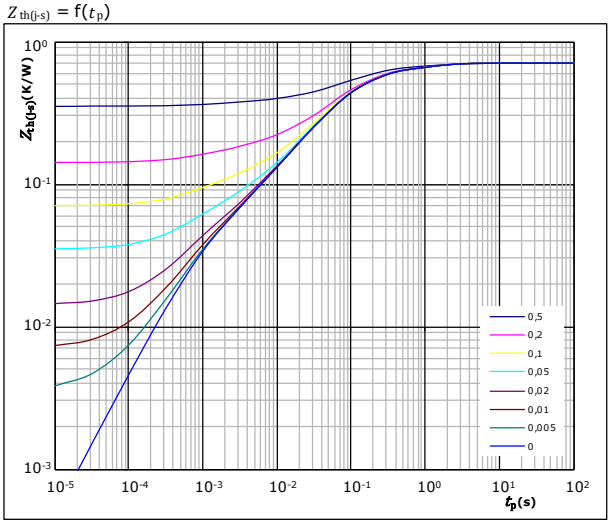


t_p =	100	µs		25 °C	
V_{CE} =	10	V	T_j:	125 °C	
				150 °C	

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	0,70	K/W

IGBT thermal model values

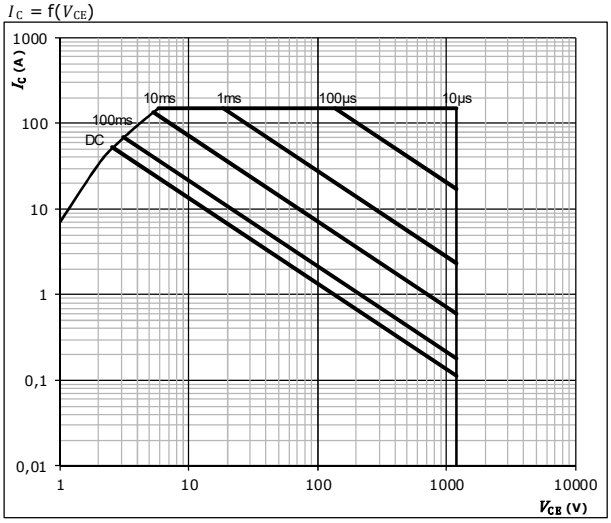
R (K/W)	τ (s)
9,44E-02	1,28E+00
1,86E-01	2,02E-01
3,33E-01	6,13E-02
5,71E-02	9,05E-03
3,26E-02	9,42E-04

Boost Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



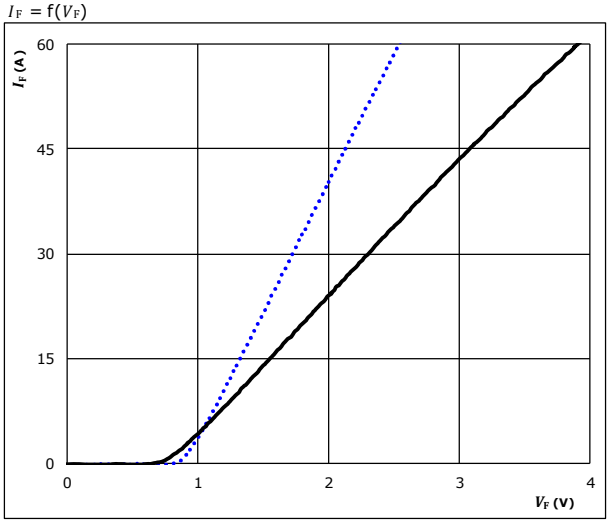
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Boost Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



t_p = 250 µs

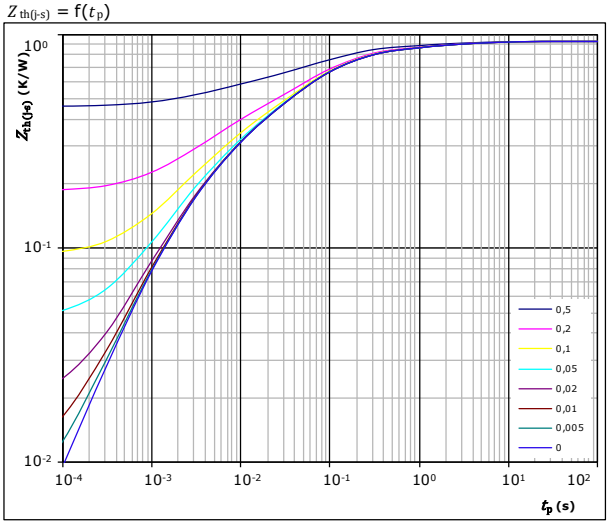
T_j: 25 °C

125 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 0,92 K/W

FWD thermal model values

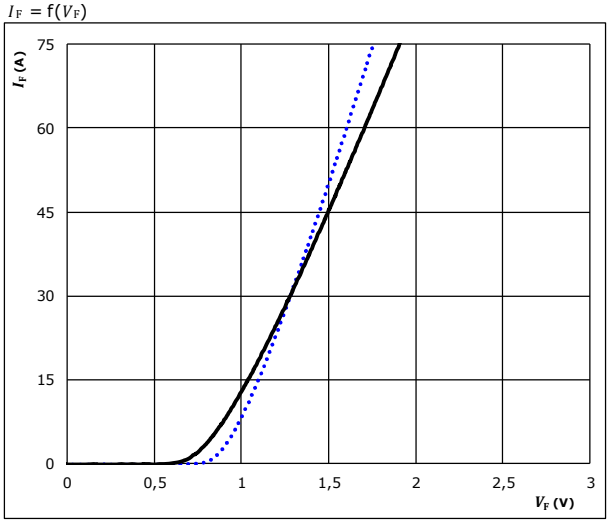
R (K/W)	τ (s)
3,98E-02	5,29E+00
8,42E-02	9,05E-01
2,67E-01	1,28E-01
2,58E-01	3,85E-02
1,93E-01	6,36E-03
7,88E-02	1,37E-03

Boost Sw. Protection Diode Characteristics

figure 1. **Rectifier Diode**

Typical forward characteristics

$I_F = f(V_F)$



t_p = 250 µs

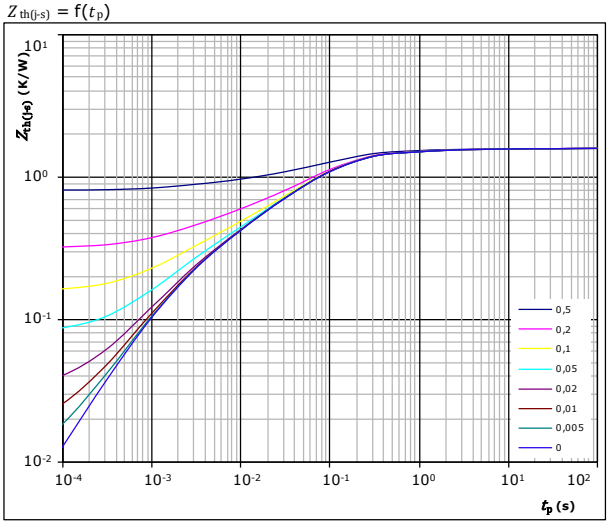
T_j: 25 °C

125 °C

figure 2. **Rectifier Diode**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,59 K/W

Diode thermal model values

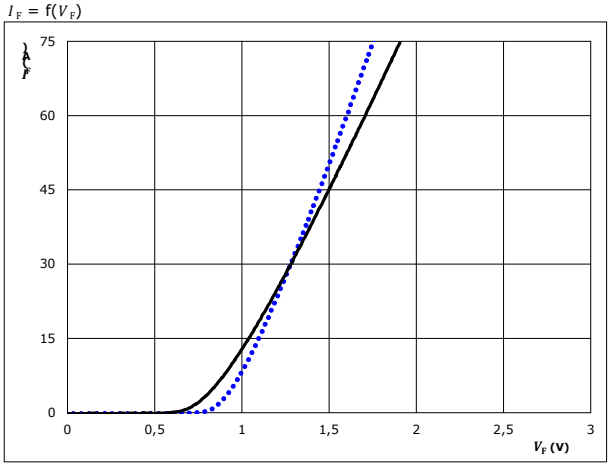
R (K/W)	τ (s)
3,44E-02	9,66E+00
1,12E-01	1,22E+00
5,81E-01	1,45E-01
4,89E-01	5,05E-02
2,38E-01	9,26E-03
1,22E-01	1,79E-03
1,81E-02	7,88E-04

ByPass Diode Characteristics

figure 1. **Rectifier Diode**

Typical forward characteristics

$I_F = f(V_F)$



t_p = 250 µs

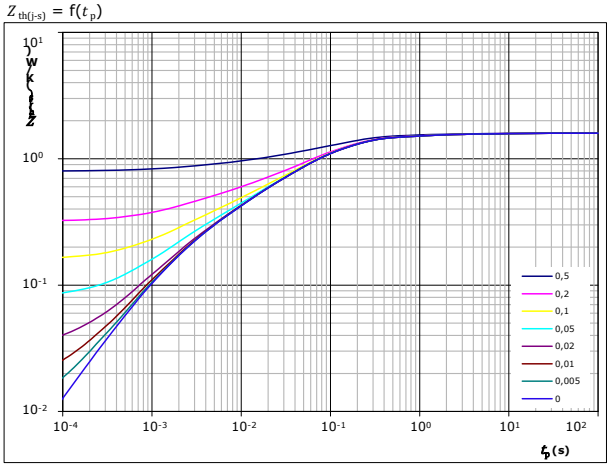
T_j: 25 °C

125 °C

figure 2. **Rectifier Diode**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,59 K/W

Diode thermal model values

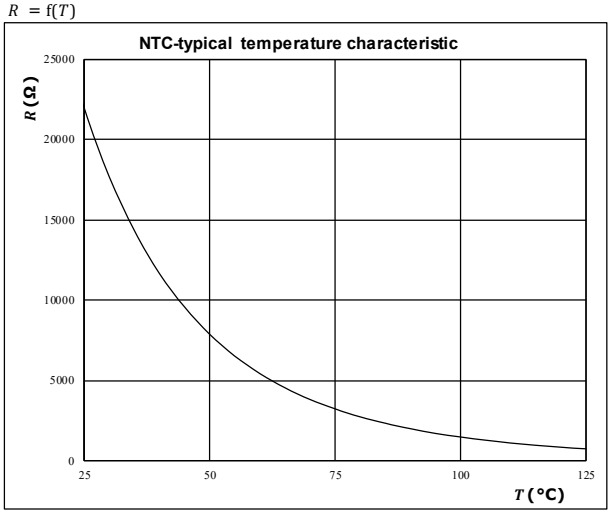
R (K/W)	τ (s)
3,44E-02	9,66E+00
1,12E-01	1,22E+00
5,81E-01	1,45E-01
4,89E-01	5,05E-02
2,38E-01	9,26E-03
1,22E-01	1,79E-03
1,81E-02	7,88E-04

Thermistor Characteristics

figure 1. **Thermistor**

Typical NTC characteristic
as a function of temperature

$R = f(T)$

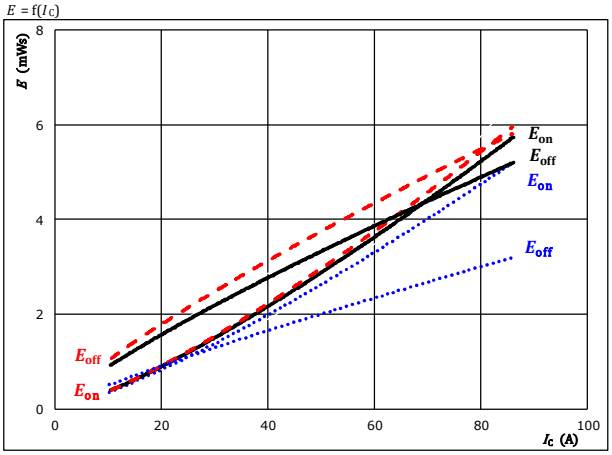


Boost Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



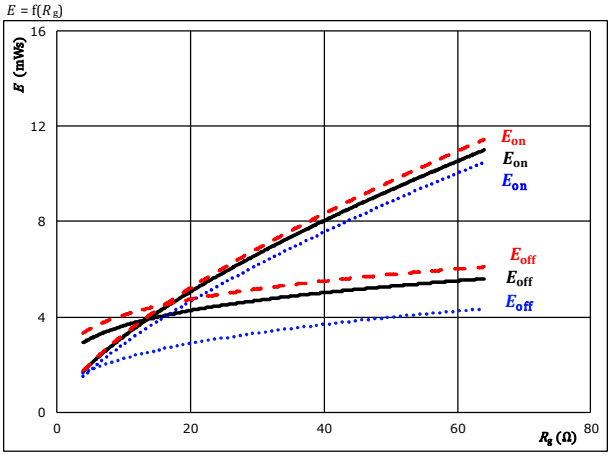
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
R_{gon} =	8	Ω		150 °C
R_{goff} =	8	Ω		

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



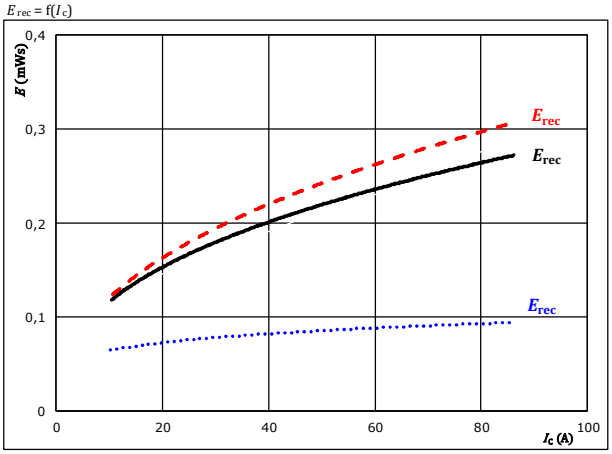
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
I_C =	50	A		150 °C

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



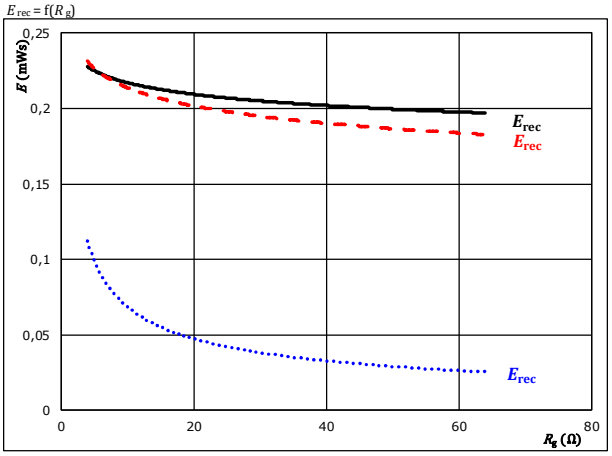
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

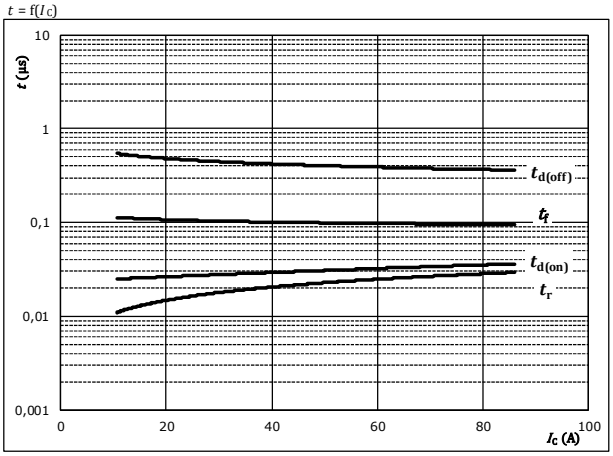
V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
I_C =	50	A		150 °C

Boost Switching Characteristics

figure 5. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



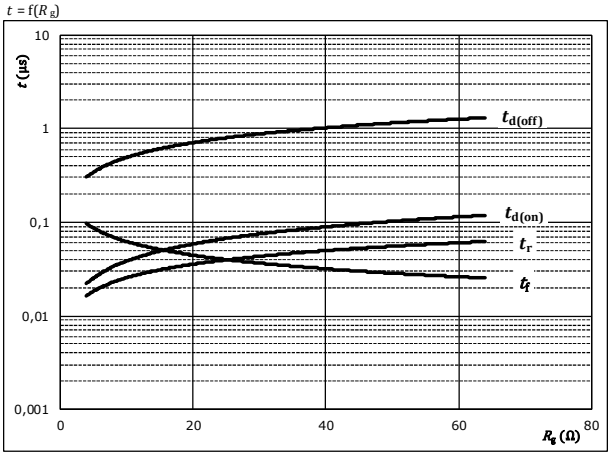
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	0 / 15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 6. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_g)$



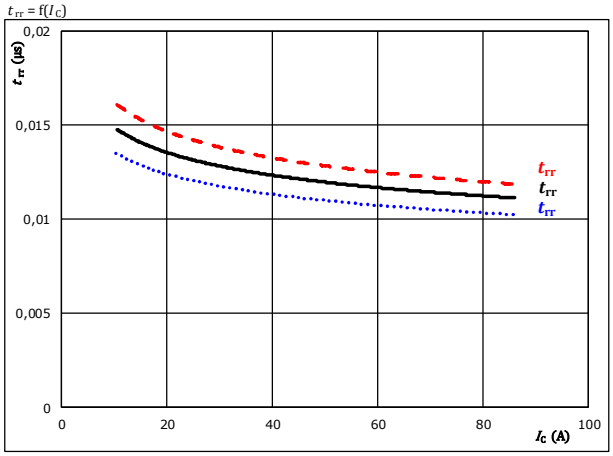
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	0 / 15	V
I_C =	50	A

figure 7. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



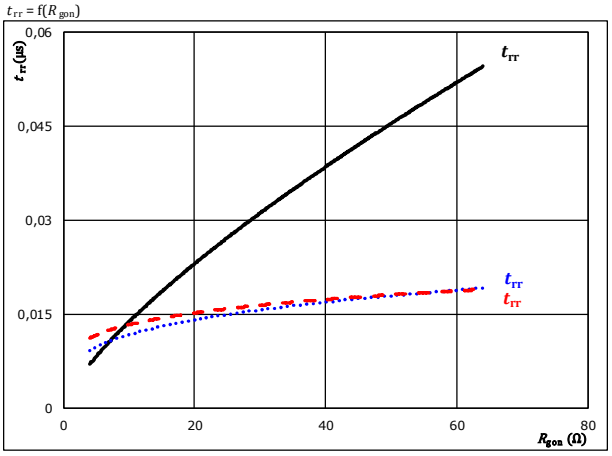
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 8. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

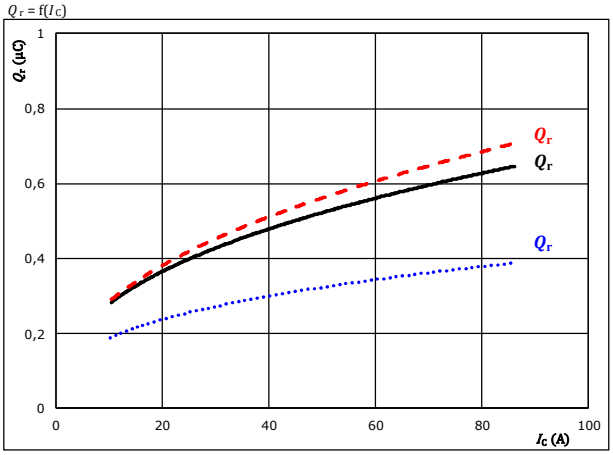
V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
I_C =	50	A		150 °C

Boost Switching Characteristics

figure 9. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$



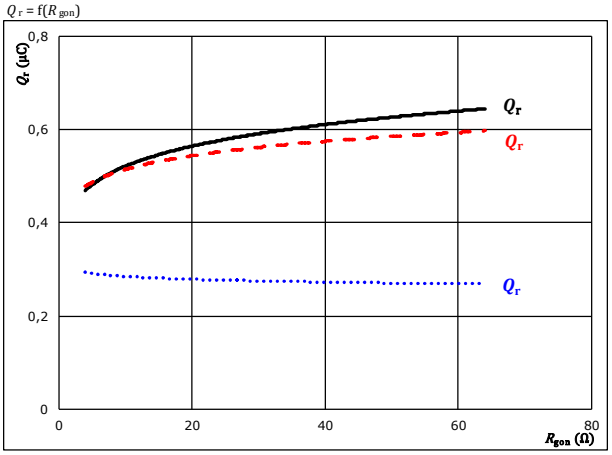
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 10. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$



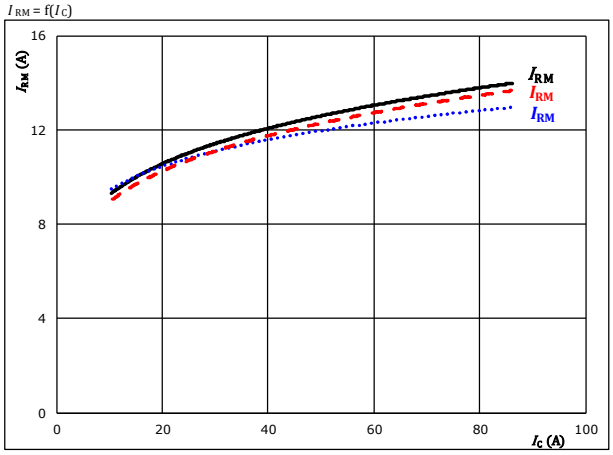
With an inductive load at

V_{CE}=	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
I_C=	50	A		150 °C

figure 11. **FWD**

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$



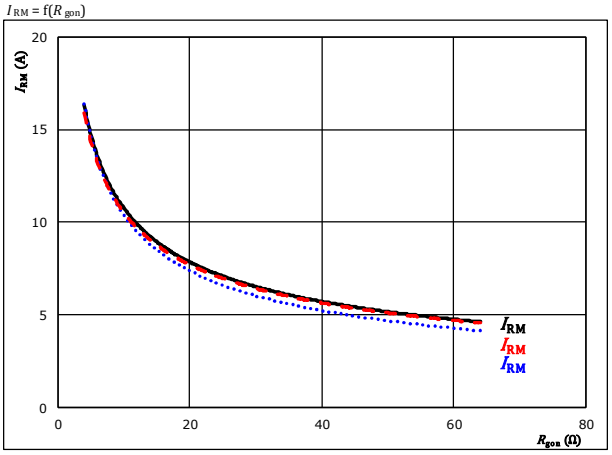
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 12. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



With an inductive load at

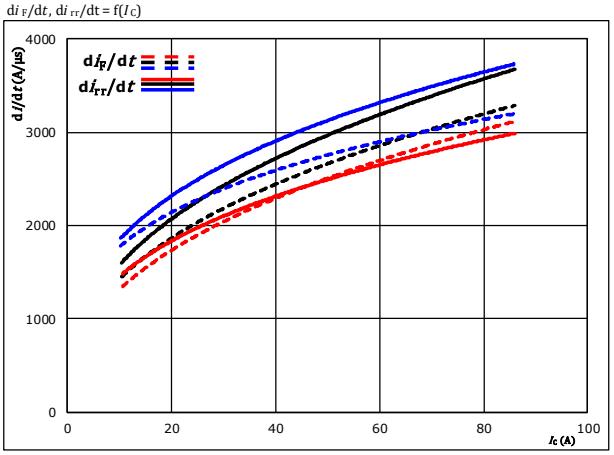
V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
I_C =	50	A		150 °C

Boost Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, $di_{rr}/dt = f(I_C)$



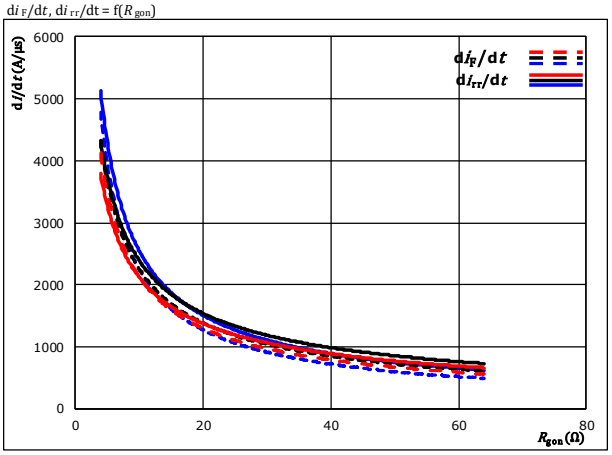
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

di_F/dt, $di_{rr}/dt = f(R_{gon})$



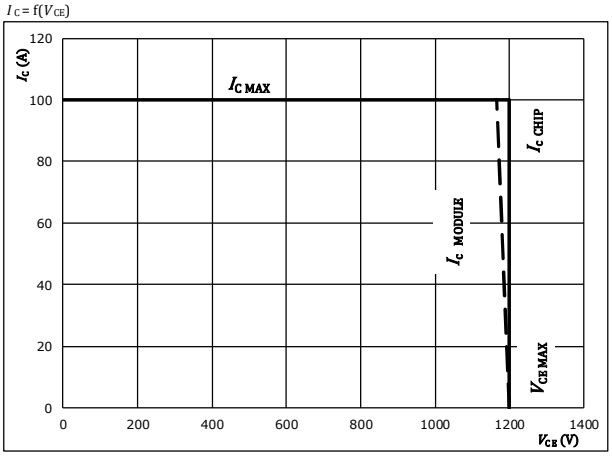
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	0 / 15	V		125 °C
I_C =	50	A		

figure 15. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j =	125	°C
R_{gon} =	8	Ω
R_{goff} =	8	Ω

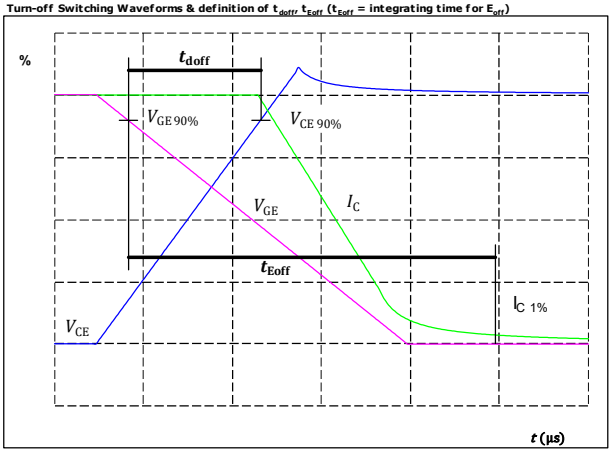
Boost Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	8 Ω
R_{goff}	=	8 Ω

figure 1. IGBT

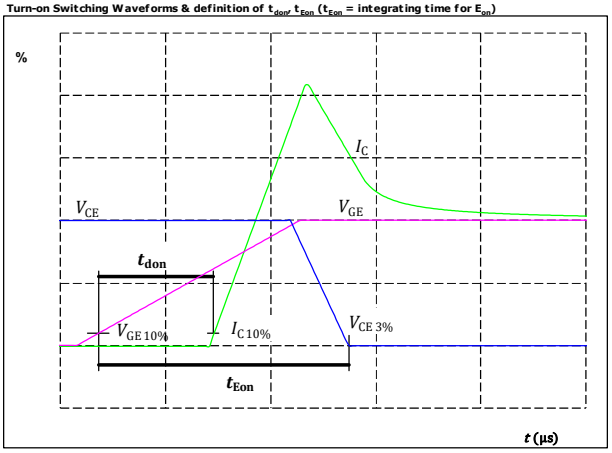
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%)$ =	0	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	700	V
$I_C(100\%)$ =	50	A
t_{doff} =	388	ns

figure 2. IGBT

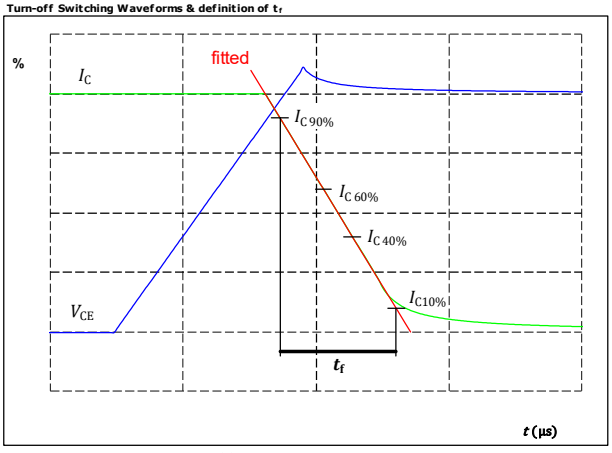
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%)$ =	0	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	700	V
$I_C(100\%)$ =	50	A
t_{don} =	30	ns

figure 3. IGBT

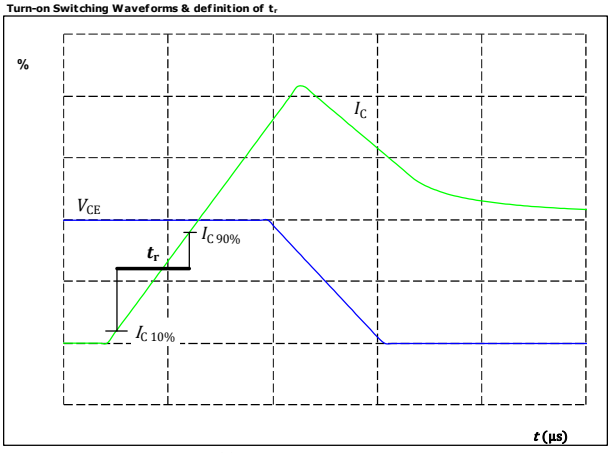
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%)$ =	700	V
$I_C(100\%)$ =	50	A
t_f =	56	ns

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

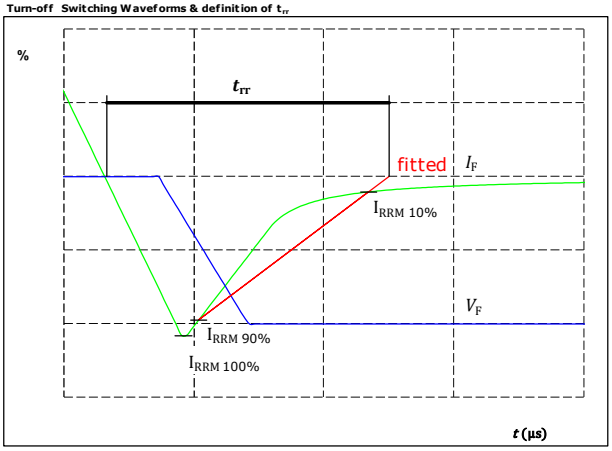


$V_C(100\%)$ =	700	V
$I_C(100\%)$ =	50	A
t_r =	21	ns

Boost Switching Characteristics

figure 5. **FWD**

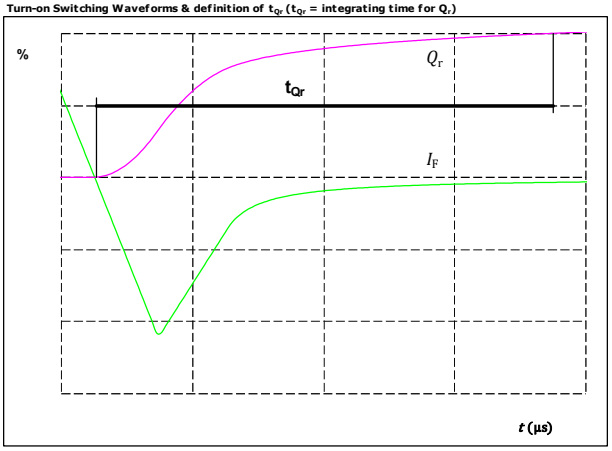
Turn-off Switching Waveforms & definition of t_{rr}



V_F (100%) =	700	V
I_F (100%) =	50	A
I_{RRM} (100%) =	12	A
t_{rr} =	12	ns

figure 6. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



I_F (100%) =	50	A
Q_r (100%) =	0,48	µC

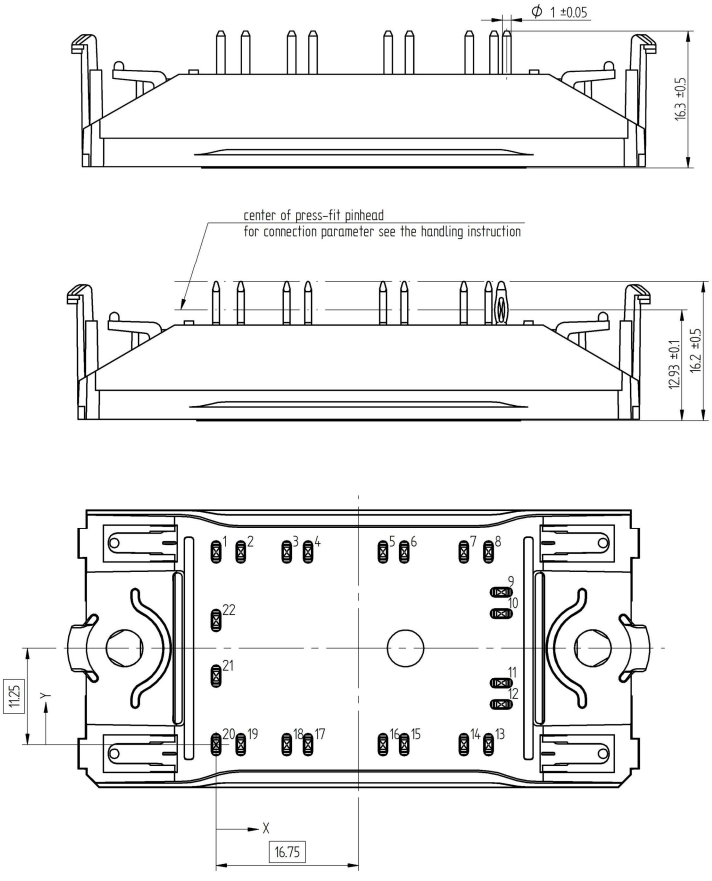
Ordering Code & Marking

Version	Ordering Code
12 mm housing with solder pin without thermal paste	V23990-P629-L57-PM
12 mm housing with pressfit pin without thermal paste	V23990-P629-L57Y-PM

Text	**VIN**	**Date code**	**Name&Ver**	**UL**	**Lot**	**Serial**
	VIN	WWYY	NNNNNNNVV	UL	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

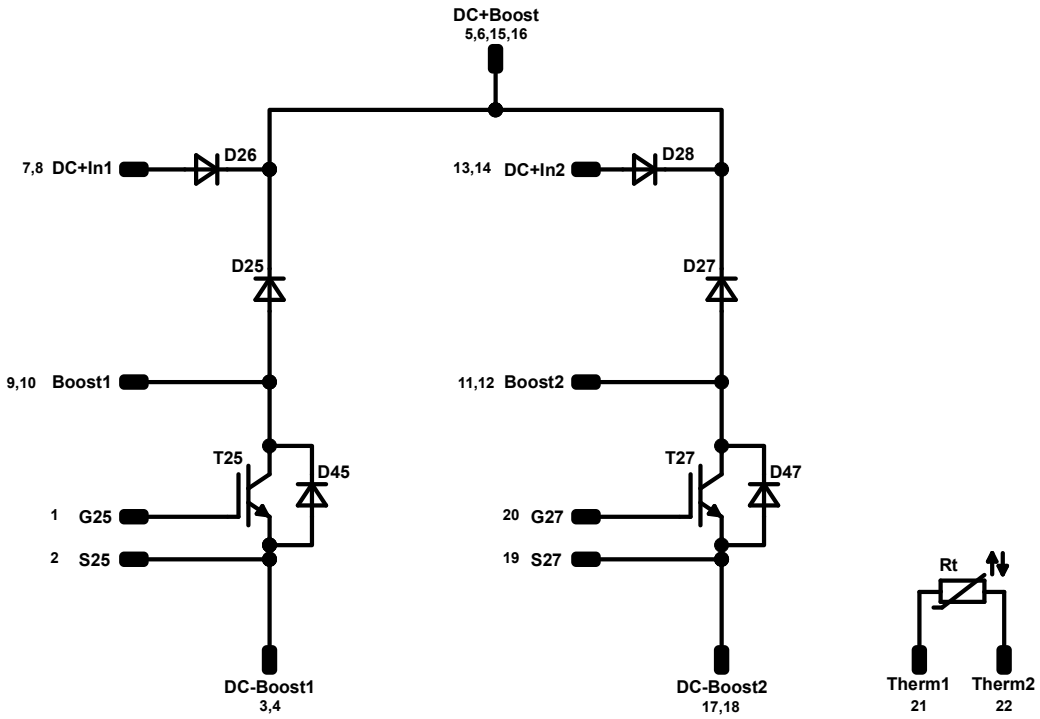
Outline

Pin table			
Pin	X	Y	Function
1	0	22,5	G25
2	2,9	22,5	S25
3	8,3	22,5	DC-Boost1
4	10,8	22,5	DC-Boost1
5	19,6	22,5	DC+Boost
6	22,1	22,5	DC+Boost
7	29,1	22,5	DC+In1
8	32	22,5	DC+In1
9	33,5	17,8	Boost1
10	33,5	15,3	Boost1
11	33,5	7,2	Boost2
12	33,5	4,7	Boost2
13	32	0	DC+In2
14	29,1	0	DC+In2
15	22,1	0	DC+Boost
16	19,6	0	DC+Boost
17	10,8	0	DC-Boost2
18	8,3	0	DC-Boost2
19	2,9	0	S27
20	0	0	G27
21	0	8	Therm1
22	0	14,5	Therm2



Tolerance of pinpositions: ±0.5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T25, T27	IGBT	1200 V	50 A	Boost Switch	
D25, D27, D25, D27	FWD	1200 V	20 A	Boost Diode	
D45, D47	FWD	1600 V	25 A	Boost Sw. Protection Diode	
D26, D28	FWD	1600 V	25 A	ByPass Diode	
Rt	NTC			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
V23990-P629-L57x-D2-14	10 Apr. 2019	Correction of I_c/I_f values	1,2